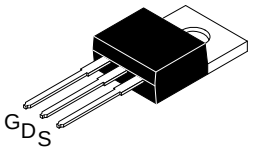
# MOSFET – N-Channel, QFET

## 200 V, 19.4 A, 150 mΩ

# FQP19N20

| $V_{DSS}$ | $R_{DS(on)}$ MAX | $I_D$ MAX |
|---|---|---|
| 200 V | 150 mΩ @ 10 V | 19.4 A |




**TO−220−3LD**
**CASE 340AT**

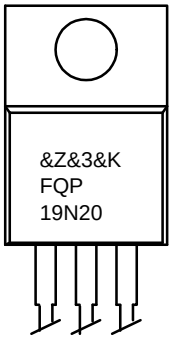
### Description

This N−Channel enhancement mode power MOSFET is produced using **onsemi**'s proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on−state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, active power factor correction (PFC), and electronic lamp ballasts.

### Features

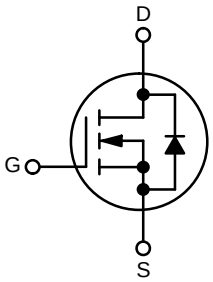
- 19.4 A, 200 V, $R_{DS(on)}$ = 150 mΩ (Max.) @ $V_{GS}$ = 10 V, $I_D$ = 9.7 A
- Low Gate Charge (Typ. 31 nC)
- Low $C_{rss}$ (Typ. 30 pF)
- 100% Avalanche Tested

### MARKING DIAGRAM




| | |
|---|---|
| &Z | = Assembly Plant Code |
| &3 | = 3−Digit Date Code |
| &K | = 2−Digits Lot Run Traceability Code |
| FQP19N20 | = Specific Device Code |

### N−CHANNEL MOSFET




### ABSOLUTE MAXIMUM RATINGS ($T_C$ = 25°C, unless otherwise noted)

| Symbol | Parameter | | FQP19N20 | Unit |
|---|---|---|---|---|
| $V_{DSS}$ | Drain−Source Voltage | | 200 | V |
| $I_D$ | Drain Current | − Continuous ($T_C$ = 25°C) | 19.4 | A |
| | | − Continuous ($T_C$ = 100°C) | 12.3 | |
| $I_{DM}$ | Drain Current | − Pulsed (Note 1) | 78 | A |
| $V_{GSS}$ | Gate−Source Voltage | | ±30 | V |
| $E_{AS}$ | Single Pulsed Avalanche Energy (Note 2) | | 250 | mJ |
| $I_{AR}$ | Avalanche Current (Note 1) | | 19.4 | A |
| $E_{AR}$ | Repetitive Avalanche Energy (Note 1) | | 14 | mJ |
| dv/dt | Peak Diode Recovery dv/dt (Note 3) | | 5.5 | V/ns |
| $P_D$ | Power Dissipation | ($T_C$ = 25°C) | 140 | W |
| | | − Derate above 25°C | 1.12 | W/°C |
| $T_J$, $T_{STG}$ | Operating and Storage Temperature Range | | −55 to +150 | °C |
| $T_L$ | Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds | | 300 | °C |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. L = 1.0 mH, $I_{AS}$ = 19.4 A, $V_{DD}$ = 50 V, $R_G$ = 25 Ω, starting $T_J$ = 25°C.
3. $I_{SD}$ ≤ 19.4 A, di/dt ≤ 300 A/μs, $V_{DD}$ ≤ $BV_{DSS}$, starting $T_J$ = 25°C.

### ORDERING INFORMATION

| Part Number | Package | Shipping |
|---|---|---|
| FQP19N20 | TO−220−3LD (Pb−Free, Halide Free) | 1000 Units / Tube |

## THERMAL CHARACTERISTICS

| Symbol | Parameter | FQP19N20 | Unit |
|---|---|---|---|
| $R_{\theta JC}$ | Thermal Resistance, Junction−to−Case, Max. | 0.89 | °C/W |
| $R_{\theta JA}$ | Thermal Resistance, Junction−to−Ambient, Max. | 62.5 | °C/W |

## ELECTRICAL CHARACTERISTICS ($T_C$ = 25°C unless otherwise noted)

| Symbol | Parameter | Test Conditions | Min | Typ | Max | Unit |
|---|---|---|---|---|---|---|
| **OFF CHARACTERISTICS** | | | | | | |
| $BV_{DSS}$ | Drain−Source Breakdown Voltage | $V_{GS}$ = 0 V, $I_D$ = 250 μA | 200 | − | − | V |
| $\Delta BV_{DSS}$ / $\Delta T_J$ | Breakdown Voltage Temperature Coefficient | $I_D$ = 250 μA, Referenced to 25°C | − | 0.18 | − | V/°C |
| $I_{DSS}$ | Zero Gate Voltage Drain Current | $V_{DS}$ = 200 V, $V_{GS}$ = 0 V | − | − | 1 | μA |
| | | $V_{DS}$ = 160 V, $T_C$ = 125°C | − | − | 10 | |
| $I_{GSSF}$ | Gate−Body Leakage Current, Forward | $V_{GS}$ = 30 V, $V_{DS}$ = 0 V | − | − | 100 | nA |
| $I_{GSSR}$ | Gate−Body Leakage Current, Reverse | $V_{GS}$ = −30 V, $V_{DS}$ = 0 V | − | − | −100 | nA |
| **ON CHARACTERISTICS** | | | | | | |
| $V_{GS(th)}$ | Gate Threshold Voltage | $V_{DS}$ = $V_{GS}$, $I_D$ = 250 μA | 3.0 | − | 5.0 | V |
| $R_{DS(on)}$ | Static Drain−Source On−Resistance | $V_{GS}$ = 10 V, $I_D$ = 9.7 A | − | 0.12 | 0.15 | Ω |
| $g_{FS}$ | Forward Transconductance | $V_{DS}$ = 40 V, $I_D$ = 9.7 A | − | 14.5 | − | S |
| **DYNAMIC CHARACTERISTICS** | | | | | | |
| $C_{iss}$ | Input Capacitance | $V_{DS}$ = 25 V, $V_{GS}$ = 0 V, f = 1.0 MHz | − | 1220 | 1600 | pF |
| $C_{oss}$ | Output Capacitance | | − | 220 | 290 | pF |
| $C_{rss}$ | Reverse Transfer Capacitance | | − | 30 | 40 | pF |
| **SWITCHING CHARACTERISTICS** | | | | | | |
| $t_{d(on)}$ | Turn−On Delay Time | $V_{DD}$ = 100 V, $I_D$ = 19.4 A, $R_G$ = 25 Ω (Note 4) | − | 20 | 50 | ns |
| $t_r$ | Turn−On Rise Time | | − | 190 | 390 | ns |
| $t_{d(off)}$ | Turn−Off Delay Time | | − | 55 | 120 | ns |
| $t_f$ | Turn−Off Fall Time | | − | 80 | 170 | ns |
| $Q_g$ | Total Gate Charge | $V_{DS}$ = 160 V, $I_D$ = 19.4 A, $V_{GS}$ = 10 V (Note 4) | − | 31 | 40 | nC |
| $Q_{gs}$ | Gate−Source Charge | | − | 8.6 | − | nC |
| $Q_{gd}$ | Gate−Drain Charge | | − | 13.5 | − | nC |
| **DRAIN−SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS** | | | | | | |
| $I_S$ | Maximum Continuous Drain−Source Diode Forward Current | | − | − | 19.4 | A |
| $I_{SM}$ | Maximum Pulsed Drain−Source Diode Forward Current | | − | − | 78 | A |
| $V_{SD}$ | Drain−Source Diode Forward Voltage | $V_{GS}$ = 0 V, $I_S$ = 19.4 A | − | − | 1.5 | V |
| $t_{rr}$ | Reverse Recovery Time | $V_{GS}$ = 0 V, $I_S$ = 19.4 A, $dI_F/dt$ = 100 A/μs | − | 140 | − | ns |
| $Q_{rr}$ | Reverse Recovery Charge | | − | 0.69 | − | μC |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

4. Essentially independent of operating temperature

## TYPICAL CHARACTERISTICS

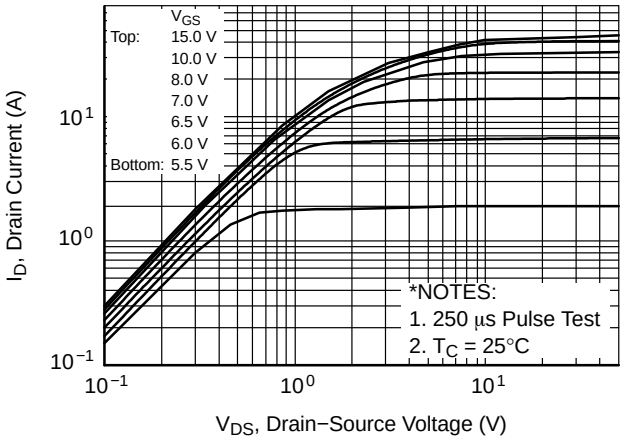



**Figure 1. On−Region Characteristics**

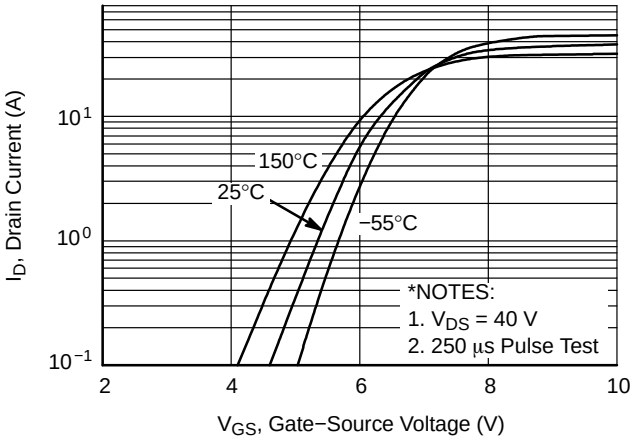



**Figure 2. Transfer Characteristics**

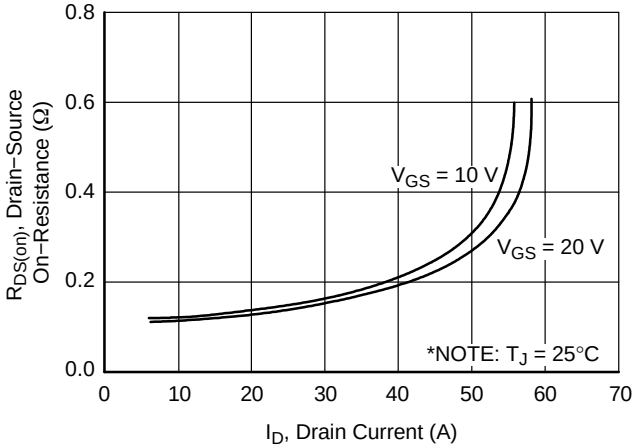



**Figure 3. On−Resistance Variation vs. Drain Current and Gate Voltage**

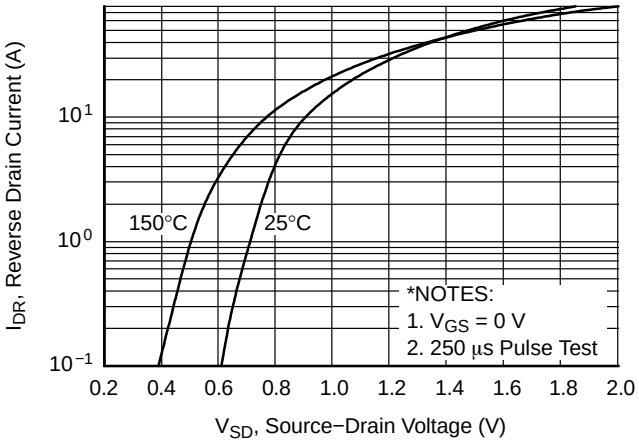



**Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature**

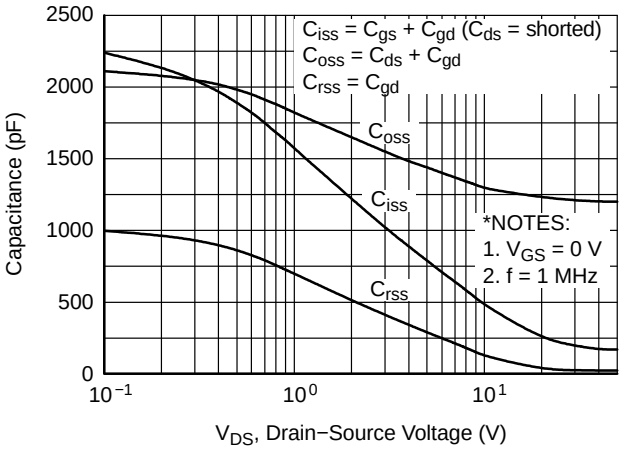



**Figure 5. Capacitance Characteristics**

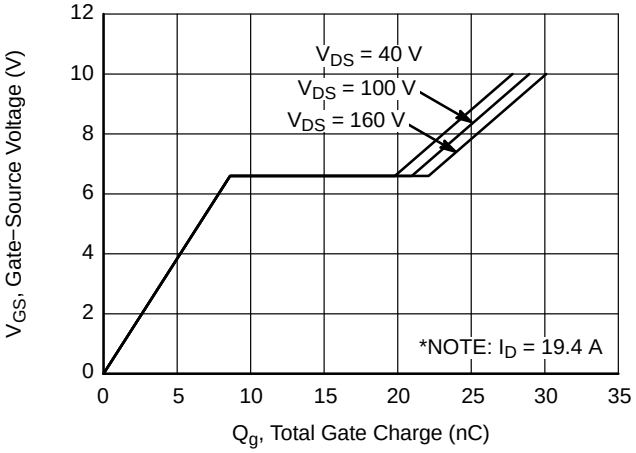



**Figure 6. Gate Charge Characteristics**

## TYPICAL CHARACTERISTICS (CONTINUED)

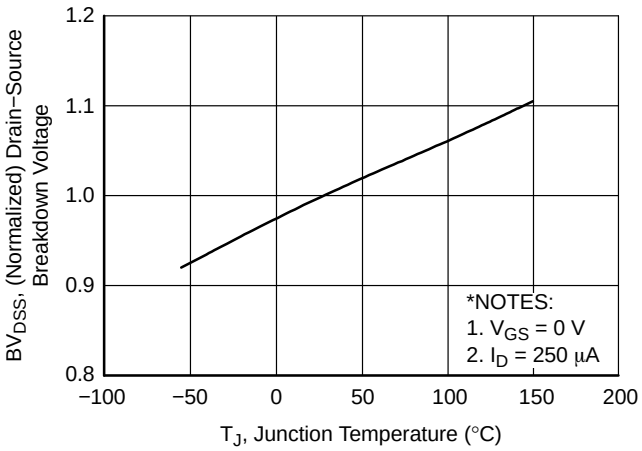



**Figure 7. Breakdown Voltage Variation vs. Temperature**

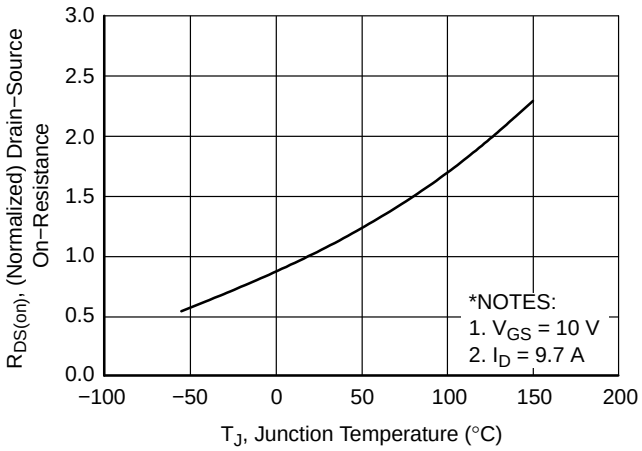



**Figure 8. On−Resistance Variation vs. Temperature**

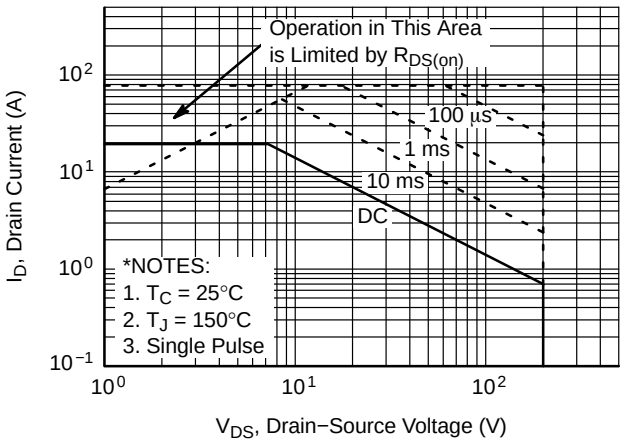



**Figure 9. Maximum Safe Operating Area**

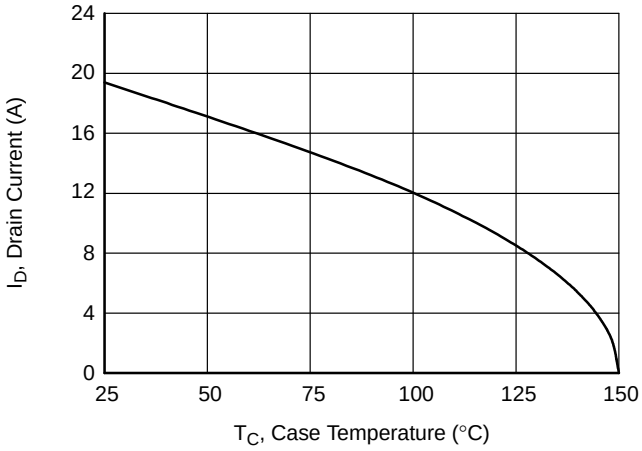



**Figure 10. Maximum Drain Current vs. Case Temperature**

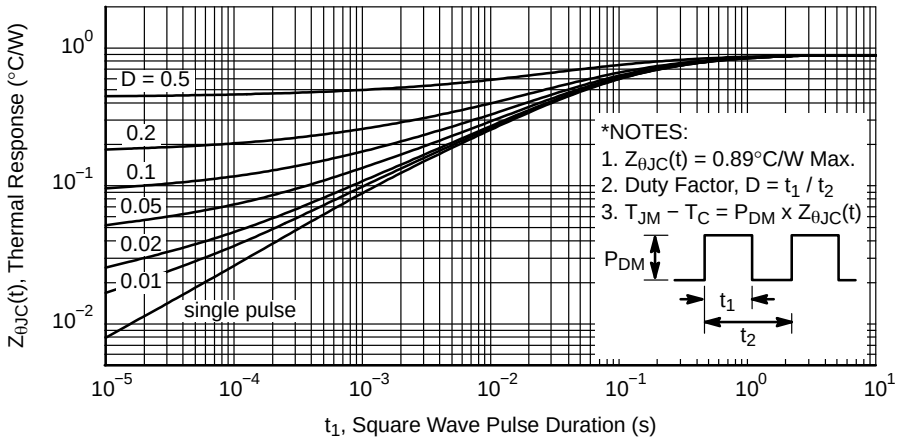



**Figure 11. Transient Thermal Response Curve**

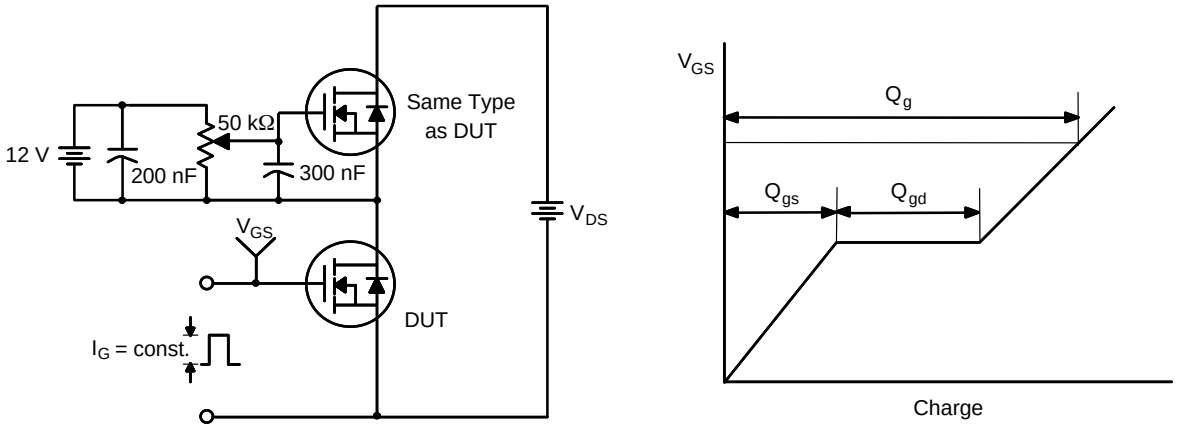



**Figure 12. Gate Charge Test Circuit & Waveform**

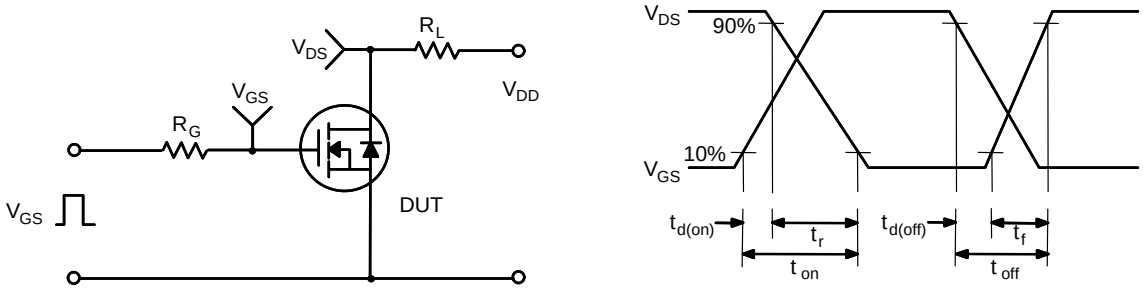



**Figure 13. Resistive Switching Test Circuit & Waveforms**

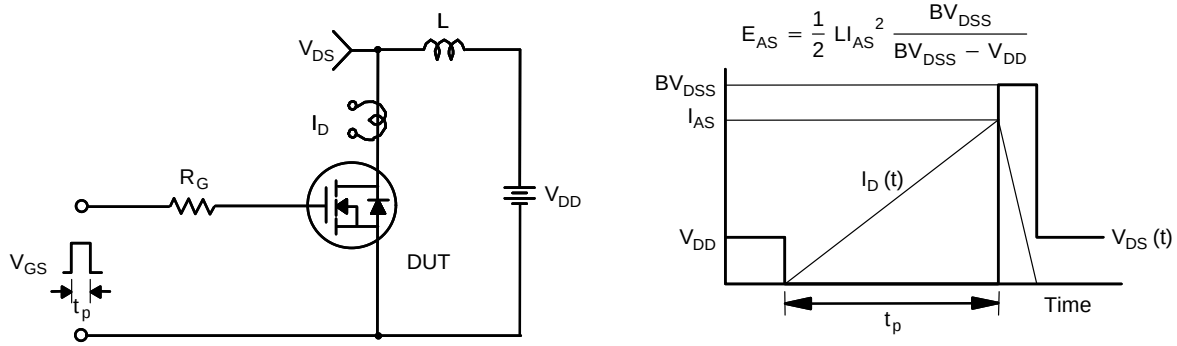



**Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms**

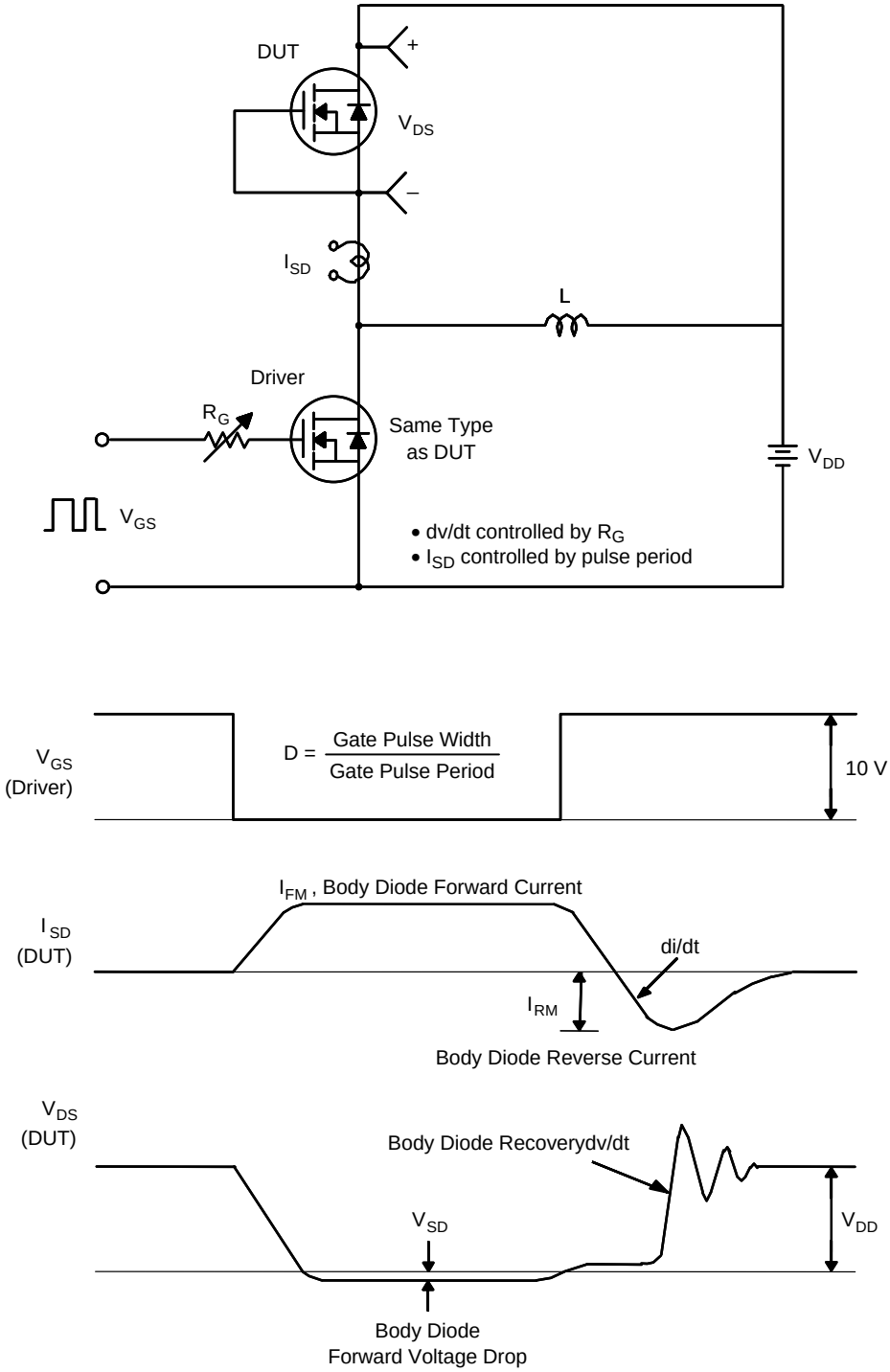


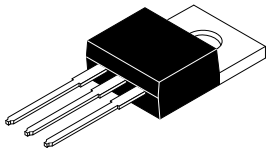

**Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms**

# MECHANICAL CASE OUTLINE
## PACKAGE DIMENSIONS

ON Semiconductor®

**TO−220−3LD**
CASE 340AT
ISSUE A

DATE 03 OCT 2017



Scale 1:1




NOTES:
A) REFERENCE JEDEC, TO-220, VARIATION AB
B) ALL DIMENSIONS ARE IN MILLIMETERS.
C) DIMENSIONS COMMON TO ALL PACKAGE SUPPLIERS EXCEPT WHERE NOTED [ ].
D) LOCATION OF MOLDED FEATURE MAY VARY (LOWER LEFT CORNER, LOWER CENTER AND CENTER OF THE PACKAGE)
E DOES NOT COMPLY JEDEC STANDARD VALUE.
F) "A1" DIMENSIONS AS BELOW:
SINGLE GAUGE = 0.51 - 0.61
DUAL GAUGE = 1.10 - 1.45
G PRESENCE IS SUPPLIER DEPENDENT
H) SUPPLIER DEPENDENT MOLD LOCKING HOLES IN HEATSINK.

| | | |
|---|---|---|
| **DOCUMENT NUMBER:** | **98AON13818G** | Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red. |
| **DESCRIPTION:** | **TO−220−3LD** | **PAGE 1 OF 1** |

## ADDITIONAL INFORMATION

**TECHNICAL PUBLICATIONS**:
**Technical Library:** www.onsemi.com/design/resources/technical−documentation
**onsemi Website:** www.onsemi.com

**ONLINE SUPPORT**: www.onsemi.com/support
**For additional information, please contact your local Sales Representative at** www.onsemi.com/support/sales